

**Silicon PNP Power Transistors****2SA877 2SA878****DESCRIPTION**

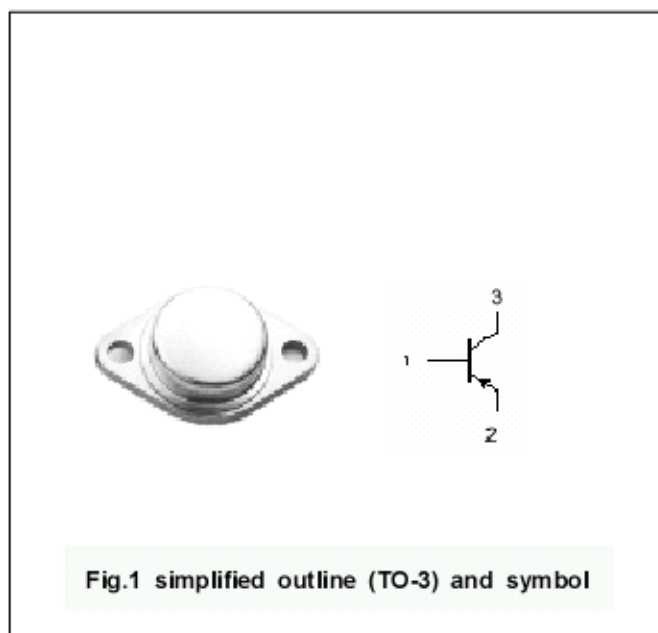
- With TO-3 package
- High power dissipation

APPLICATIONS

- Power amplifier applications
- Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Fig.1 simplified outline (TO-3) and symbol****Absolute maximum ratings(Ta=℃)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SA877	Open emitter	-80	V
		2SA878		-120	
V_{CEO}	Collector-emitter voltage	2SA877	Open base	-80	V
		2SA878		-120	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-10	A
P_C	Collector power dissipation		$T_C=25^{\circ}\text{C}$	100	W
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃



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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA877	I _C =-0.1A ; I _B =0	-80			V
		2SA878		-120			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-1mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-5A; I _B =-0.5A			-2.0	V
I _{CBO}	Collector cut-off current	2SA877	V _{CB} =-80V; I _E =0			-0.1	mA
		2SA878	V _{CB} =-120V; I _E =0				
I _{EBO}	Emitter cut-off current		V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE}	DC current gain		I _C =-3A ; V _{CE} =-4V	50			
C _{OB}	Output capacitance		I _E =0 ; V _{CB} =-10V; f=1.0MHz		255		pF
f _T	Transition frequency		I _C =-1A ; V _{CE} =-12V		15		MHz



PACKAGE OUTLINE

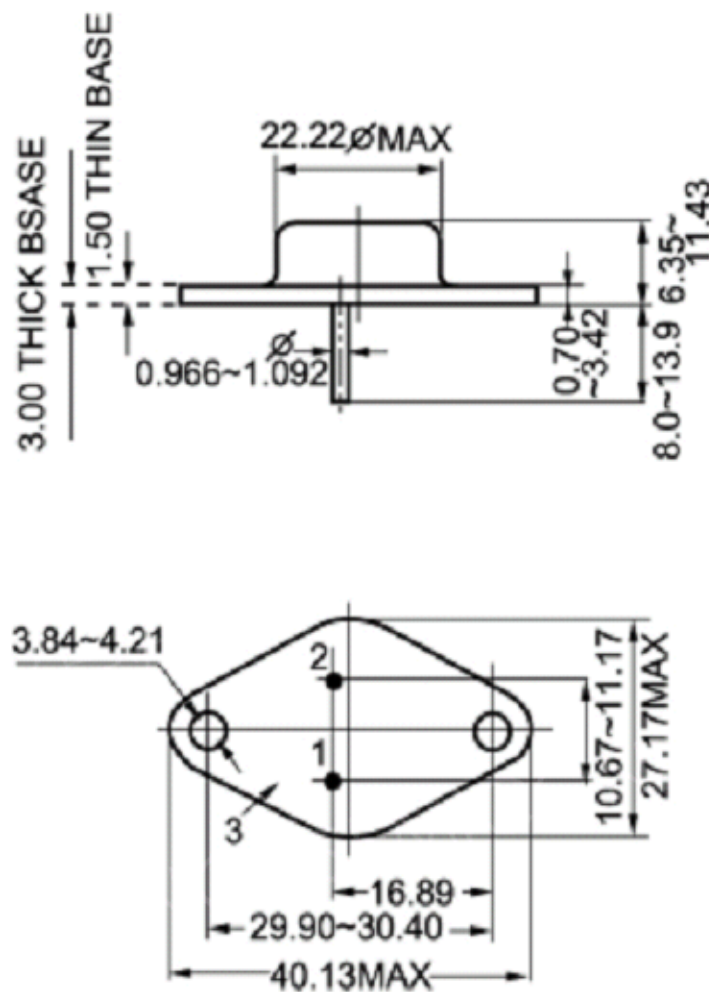


Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)